TOSHIBA Photocoupler GaAs Ired & Photo-MOS FET

# **TLP3110**

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#### Measurement Instruments

Logic IC Testers / Memory Testers

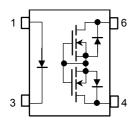
**Board Testers / Scanners** 

The TOSHIBA mini flat photo relay TLP3110 is a small outline photo relay, suitable for surface mount assembly.

The TLP3110 consists of a GaAs infrared emitting diode optically coupled to a photo–MOSFET in a 4 pin lead package (MFSOP6), and has characteristics of small off–state current and small output terminal capacitance, which enable the TLP3110 to be applied to measurement instruments.

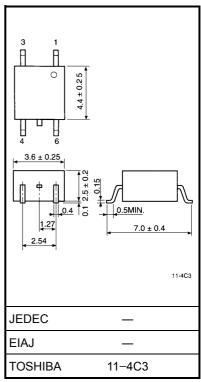
- 1-form-A
- Peak off-state voltage: 60 V (min.)
- Trigger LED current: 4 mA (max.)
- On-state current: 350 mA (max.)
- On-state resistance: 1.2 Ω (max.)
- Isolation voltage: 1500 V<sub>rms</sub> (min.)

#### Pin Configuration (top view)



- 1 : Anode
- 3: Cathode
- 4 : Drain
- 6 : Drain

Unit in mm



Weight: 0.1 g

## **Maximum Ratings (Ta = 25°C)**

	Characteristic	Symbol	Rating	Unit
	Forward current	l <sub>F</sub>	50	mA
LED	Reverse voltage		6	V
	Junction temperature	Tj	125	°C
or	Off-state output voltage	V <sub>OFF</sub>	60	V
Detector	On-state current	I <sub>ON</sub>	350	mA
ă	Junction temperature	Tj	125	°C
Sto	rage temperature	T <sub>stg</sub>	-40~125	°C
Оре	erating temperature	T <sub>opr</sub>	-20~85	°C
Lea	d soldering temperature (10 s)	T <sub>sol</sub>	260	°C
Isol	ation voltage (AC, 1 min., R.H.≤ 60%) (Note 1)	BV <sub>S</sub>	1500	V <sub>rms</sub>

(Note 1): Device considered a two–terminal device: Pins 1 and 3 shorted together, and pins 4 and 6 shorted together.

#### **Recommended Operating Conditions**

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V <sub>OFF</sub>	_	_	48	V
Forward current	l <sub>F</sub>	10	_	30	mA
On-state current	I <sub>ON</sub>	_	_	350	mA
Operating temperature	T <sub>opr</sub>	25	_	50	°C

#### **Individual Electrical Characteristics (Ta = 25°C)**

Characteristic		Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 20 mA	1.0	1.2	1.4	V
LED	Reverse voltage	I <sub>R</sub>	V <sub>R</sub> = 6 V	_	_	10	μΑ
	Capacitance	C <sub>T</sub>	V = 0, f = 1 MHz	1	15	-	pF
Detector	Off-state current	l <sub>OFF</sub>	V <sub>OFF</sub> = 30 V, Ta = 50 °C	-	0.4	1	nA
Dete	Capacitance	C <sub>OFF</sub>	V = 0, f = 1 MHz	_	100	150	pF

## **Coupled Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Condition	MIn.	Тур.	Max.	Unit
Trigger LED current	I <sub>FT</sub>	I <sub>ON</sub> = 350 mA	_	_	4	mA
On-state resistance	R <sub>ON</sub>	I <sub>ON</sub> = 350 mA, I <sub>F</sub> = 5 mA	_	0.9	1.2	Ω

# Isolation Characteristics (Ta = 25°C)

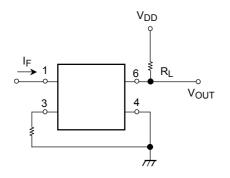
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	Cs	V <sub>S</sub> = 0 V, f = 1 MHz	_	8.0	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V, R.H. ≤ 60%	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
		AC, 1 minute	1500	_	_	V <sub>rms</sub>
Isolation voltage	$BV_S$	AC, 1 second (in oil)	_	3000	_	v rms
		DC, 1 minute (in oil)	_	3000	_	$V_{dc}$

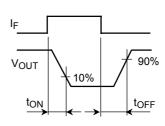
## **Switching Characteristics (Ta = 25°C)**

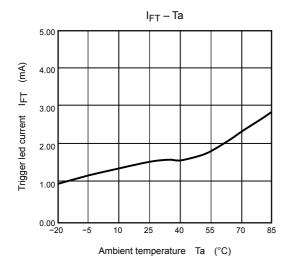
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Turn-on time	t <sub>ON</sub>	$R_L = 200\Omega$ (Note 2)	_	_	1	ms
Turn-off time	toff	$V_{DD} = 20 \text{ V}, I_F = 10 \text{ mA}$	_	_	1	1113

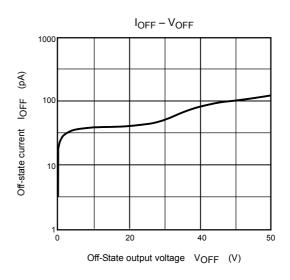
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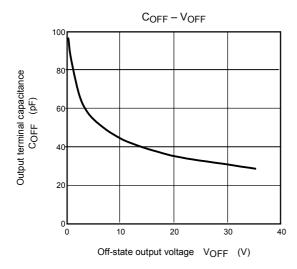
(Note 2): Switching time test circuit











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